

# Thermally and optically excited multi-channel transport at the interface of LaAlO<sub>3</sub>/SrTiO<sub>3</sub> heterostructures

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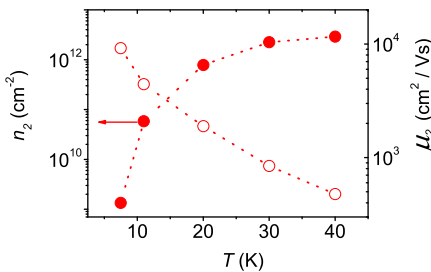
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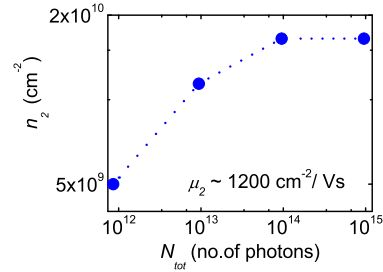
We have performed magnetotransport experiments on a LaAlO<sub>3</sub>/SrTiO<sub>3</sub> interface [1] with a 10 nm LaAlO<sub>3</sub> film, in magnetic fields up to 30 T. The temperature was varied in the range  $T = 4.2$  K to 150 K and additionally the sample was illuminated with UV radiation at a fixed  $T = 4.2$  K.

Our experimental results show that the low-temperature regime ( $T \leq 4.2$  K) is dominated by one type of charge carriers,  $n_1 \simeq 10^{14} \text{ cm}^{-2}$ , with a lower carrier mobility,  $\mu_1 \simeq 5 \text{ cm}^2/\text{Vs}$ , yielding a linear Hall resistance. Increasing  $T$  above 4.2 K or illuminating with UV light with an energy higher than the SrTiO<sub>3</sub> band-gap (3.65 eV) at a fixed  $T = 4.2$  K, leads to a significant decrease of the resistance, a strong positive magnetoresistance appears and the Hall resistance becomes distinctly non-linear. We explain our observations by thermal or optical excitation of an additional high-mobility electron channel situated 6 meV above the low-mobility channel.

Our magnetotransport data can be quantitatively explained within a simple two-carrier model, where thermal activation (Fig. a) or UV illumination (Fig. b) creates a low-concentration ( $n_2$ ) and high-mobility ( $\mu_2$ ) electron channel [2], in addition to an existing low-mobility one at 4.2 K. The carrier concentration and the mobility values of this second-electronic channel are extracted from a two-band model fits of the magnetoresistance and the non-linear Hall resistance.



(a) Concentration (left axis, filled circles) and mobility (right axis, open circles) of thermally activated high-mobility electron channel as a function of temperature.



(b) Concentration (filled circles) of the photo-excited carriers as a function of illumination intensity expressed in terms of the photon number,  $N_{tot}$ , at 4.2 K.

[1] A. Ohtomo and H. Y. Hwang, Nature **427**, 423 (2004).

[2] V. K. Guduru *et al.*, Appl. Phys. Lett. **102**, 051604 (2013).